



L Number	Hits	Search Text	DB	Time stamp
38	23	(triple adj2 well) same ( (high) with	USPAT;	2003/04/29 13:17
		(low) with (voltage or power))	US-PGPUB	i I
39	135607	((high) with (low) with (voltage or	USPAT;	2003/04/29 13:18
		power))	US-PGPUB	
-	26780	"high voltage" same "low voltage"	USPAT;	2003/04/18 13:03
! 			US-PGPUB	
-	1	("5847432").PN.	USPAT;	2003/04/18 12:13
			US-PGPUB	
-	9586	("high voltage" same "low voltage") and	USPAT;	2003/04/18 12:14
		threshold	US-PGPUB	
<del>-</del>	6913	(("high voltage" same "low voltage") and	USPAT;	2003/04/18 12:15
		threshold) and (ic or "integrated circuit"	US-PGPUB	i
		or semiconductor)		
-	68	((("high voltage" same "low voltage") and	USPAT;	2003/04/18 12:15
		threshold) and (ic or "integrated circuit"	US-PGPUB	
	00127	or semiconductor)) and (LDMOS)		0000/04/10 13 04
-	20137	"high voltage" with "low voltage"	USPAT;	2003/04/18 13:04
	4017		US-PGPUB	1 0000 (04 (10 10 05 1
-	4817	("high voltage" with "low voltage") and	USPAT;	2003/04/18 13:05
	F 77.0	((threshold near voltage) or "V.sub.th")	US-PGPUB	0000 (04 (00 11 50 )
_	573	(("high voltage" with "low voltage") and	USPAT;	2003/04/29 11:53
		((threshold near voltage) or "V.sub.th"))	US-PGPUB	
		and (doping or implanting) and		
		(concentration)		